

37-40GHz Down converter *Preliminary*

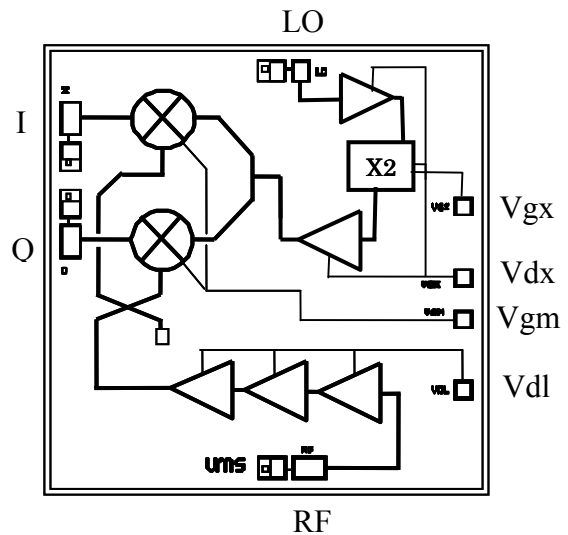
GaAs Monolithic Microwave IC in SMD package

Description

The MFC-PO13811-QDG is a multifunction part, which integrates a balanced cold FET mixer, a time two multiplier, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems.

The circuit is manufactured with a PM-HEMT process, 0.25µm gate length, via holes through the substrate and air bridges.

It is supplied in lead-free SMD package.



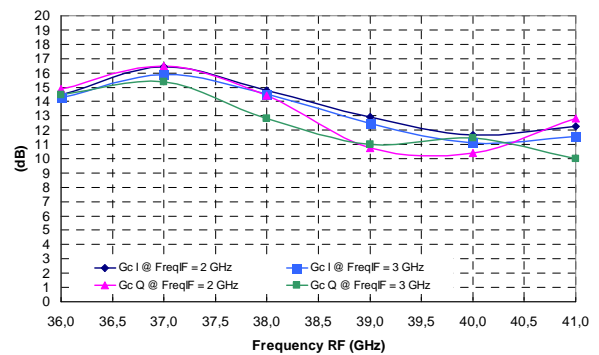
Main Features

- Broadband performance 37-40GHz
- 12dB gain
- -5dBm IIP3
- 12dBc Image Frequency Rejection
- ESD protected on LO, RF, Vgx, Vgm Accesses
- 24L-QFN4x4

Main Characteristics

Tamb. = 25°C, Vd = 4V

Conversion gain (Inf. & Sup. Mode) @PLO=1dBm



Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	37		40	GHz
F _{LO}	LO frequency range	17.5		21	GHz
F _{IF}	IF frequency range	DC		3.5	GHz
G _c	Conversion gain		12		dB

ESD Protection: Electrostatic discharge sensitive device. Observe handling precautions!

Electrical Characteristics

$T_{amb}=25^{\circ}\text{C}$, $V_{dx}=V_{dl} = 4\text{V}$, Typical $V_{gx} = -0.9\text{V}$ & $V_{gm} = -0.7\text{V}$

These values are representative of onboard measurements (on connectors access planes) as defined on the drawing 96401

Preliminary

Symbol	Parameter	Min	Typ	Max	Unit
F_{RF}	RF frequency range	37		40	GHz
F_{LO}	LO frequency range	17.5		21	GHz
F_{IF}	IF frequency range	DC		3.5	GHz
G_c	Conversion gain		12		dB
P_{LO}	LO Input power		0		dBm
Img Sup	Image Suppression (1)		12		dBc
NF	Noise Figure		4.5		dB
IIP3	Input IP3		-5		dBm
LO VSWR	Input LO VSWR		2.0:1		
RF VSWR	Input RF VSWR		1.7:1		
I_d	Bias current (2)		140		mA

(1) With external I/Q 90° hybrid coupler

(2) Typically, $I_{dl} = 60\text{mA}$, $I_{dx} = 80\text{mA}$

Absolute Maximum Ratings (1)

$T_{amb} = +25^{\circ}\text{C}$

Symbol	Parameter	Values	Unit
V_d	Maximum drain bias voltage	4.5	V
I_d	Maximum drain bias current	200	mA
V_g	Gate bias voltage	-2.0 to +0.4	V
P_{RF}	Maximum RF input power	10	dBm
P_{LO}	Maximum LO input power	10	dBm
T_{ch}	Maximum channel temperature (2)	175	$^{\circ}\text{C}$
T_a	Operating temperature range	-40 to +85	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-55 to +125	$^{\circ}\text{C}$

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Thermal Resistance channel to ground paddle = $70.6^{\circ}\text{C}/\text{W}$ for $T_{amb} = +85^{\circ}\text{C}$

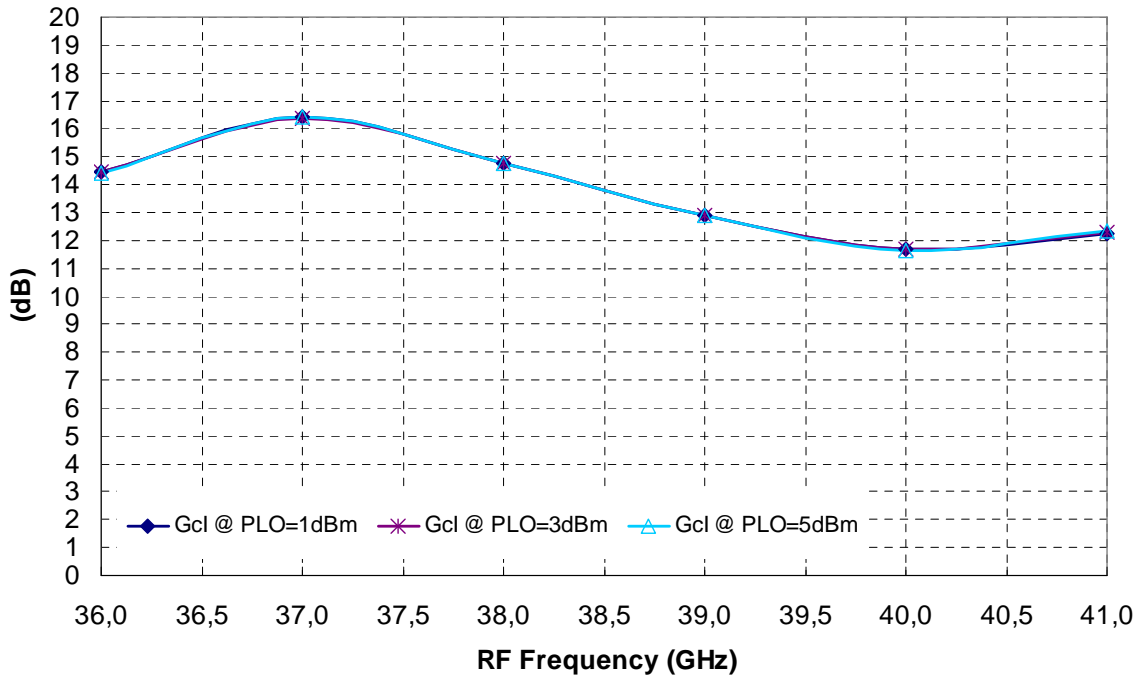
Typical Measured Performance

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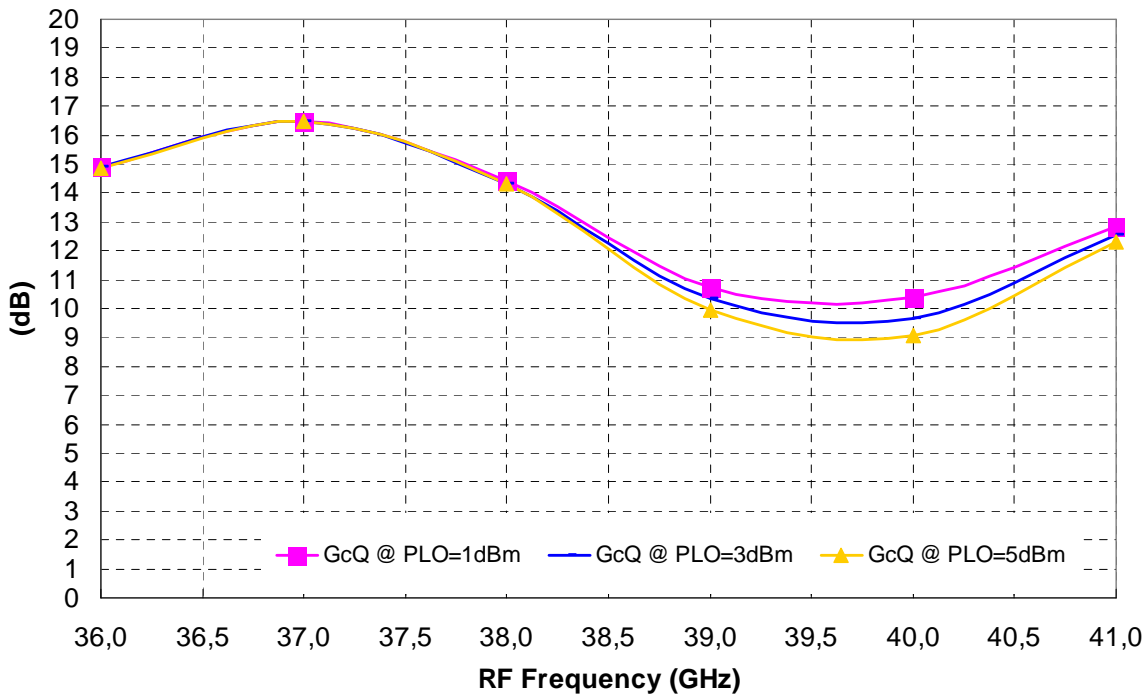
Tamb. = 25°C, Vdx=Vdl = 4V, Typical Vgx = -0.9V & Vgm= -0.7V

These values are representative of onboard measurements (on connectors access planes) as defined on the drawing 96401

Conversion Gain (infradyne mode (1)) @ Freq_IF=2GHz



Conversion Gain (supradyne mode (2)) @ Freq_IF=2GHz



- (1) Infradyne mode : $Freq_{RF} = 2 * Freq_{LO} + Freq_{IF}$
- (2) Supradyne mode : $Freq_{RF} = 2 * Freq_{LO} - Freq_{IF}$

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Conversion Gain (Inf & sup mode) @ P_{LO}=1dBm

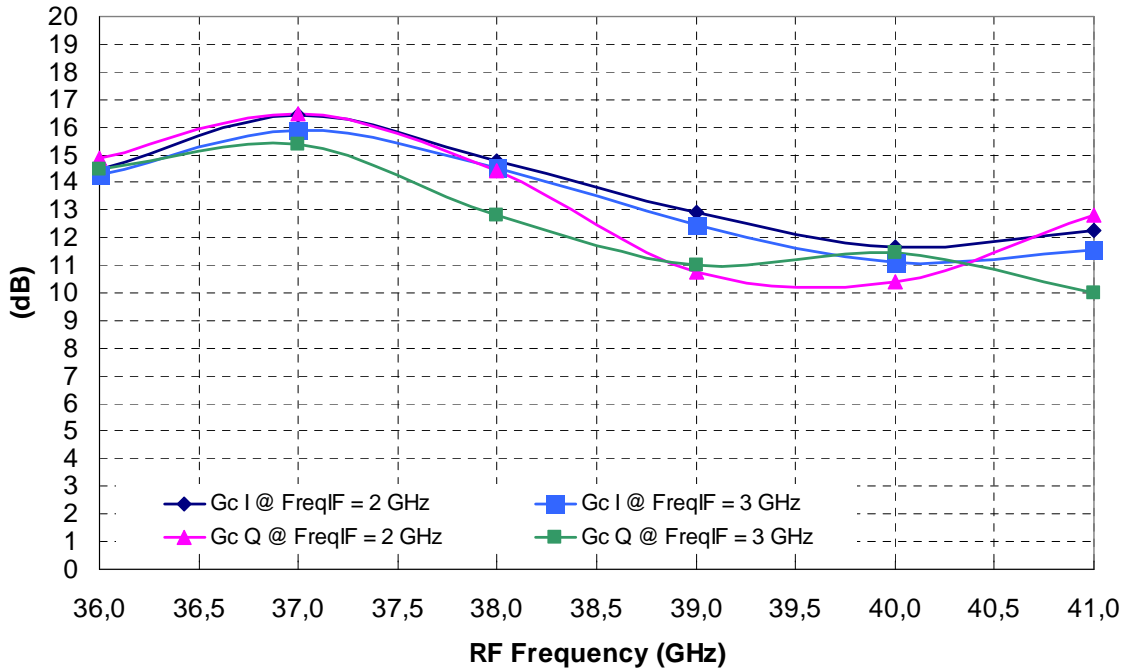
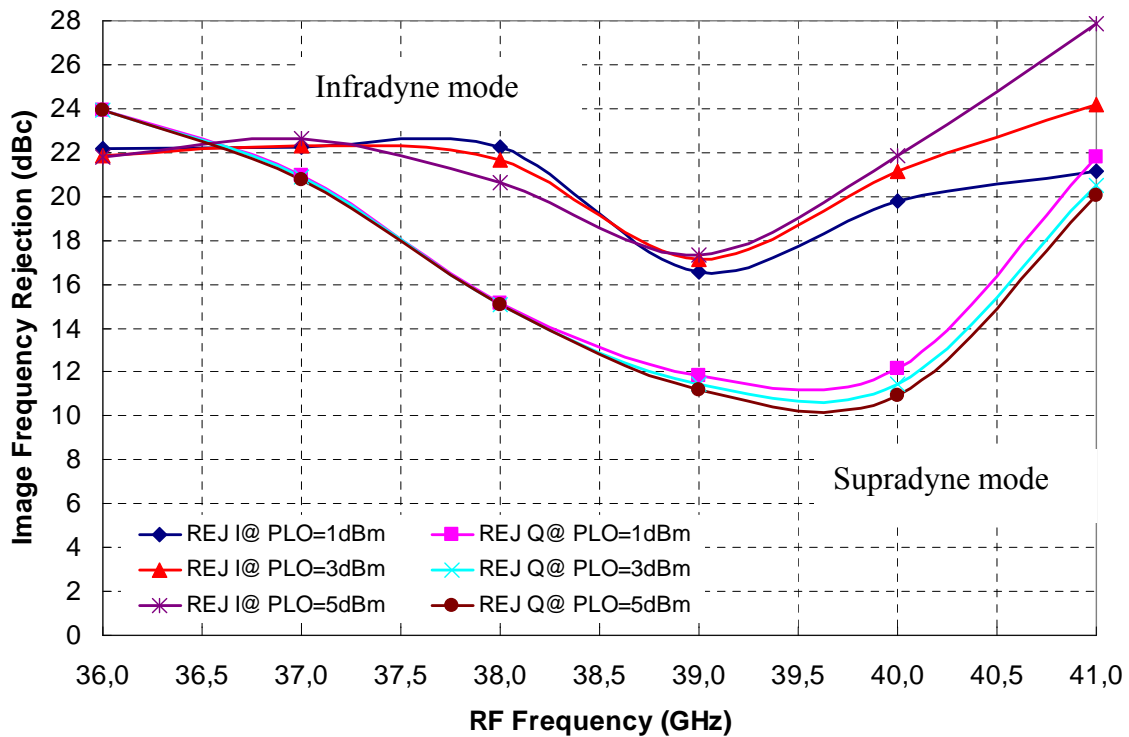
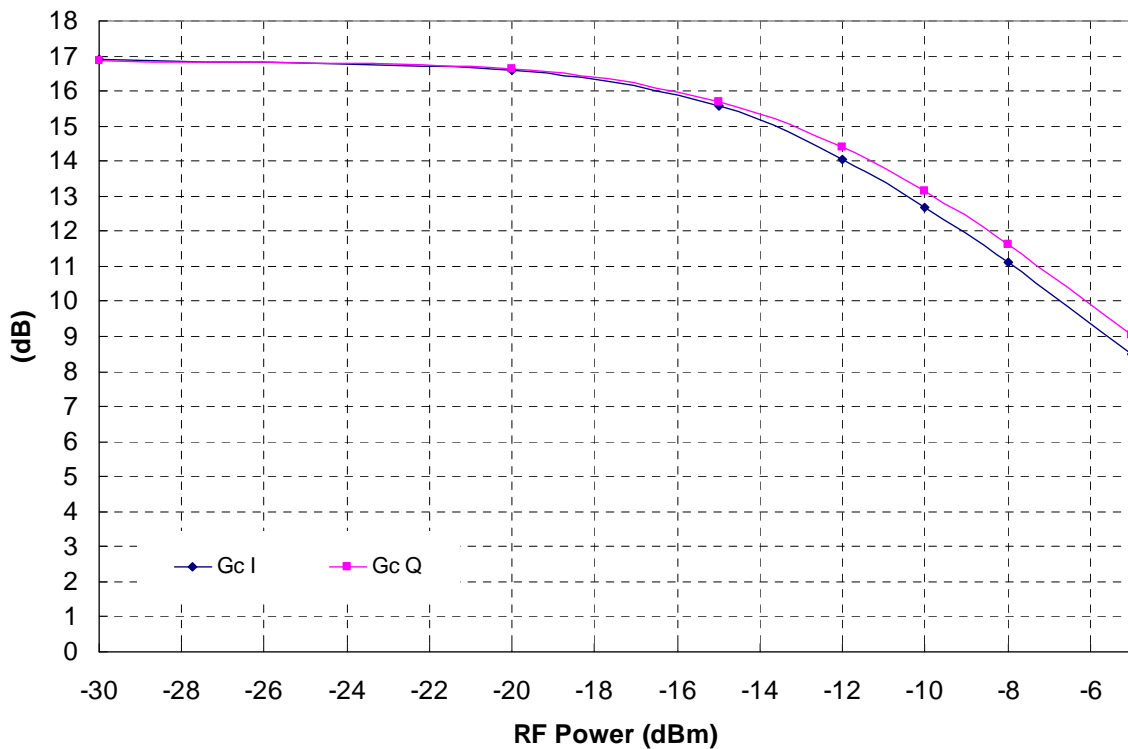


Image Frequency Rejection (inf. & sup. Mode) @ Freq FI=2GHz

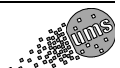
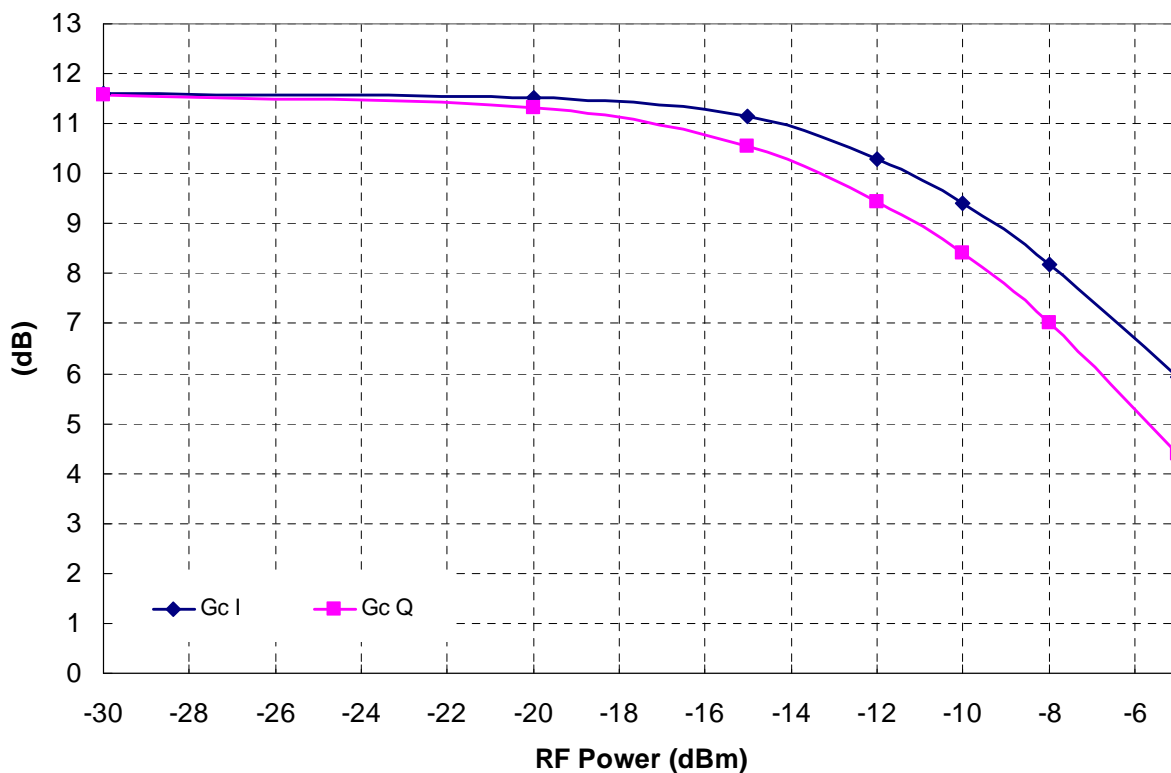


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Compression vs P_{RF} (inf. & sup. Mode)
 @ F_{RF}=37GHz & F_{IF}=2GHz & P_{LO}=0 dBm

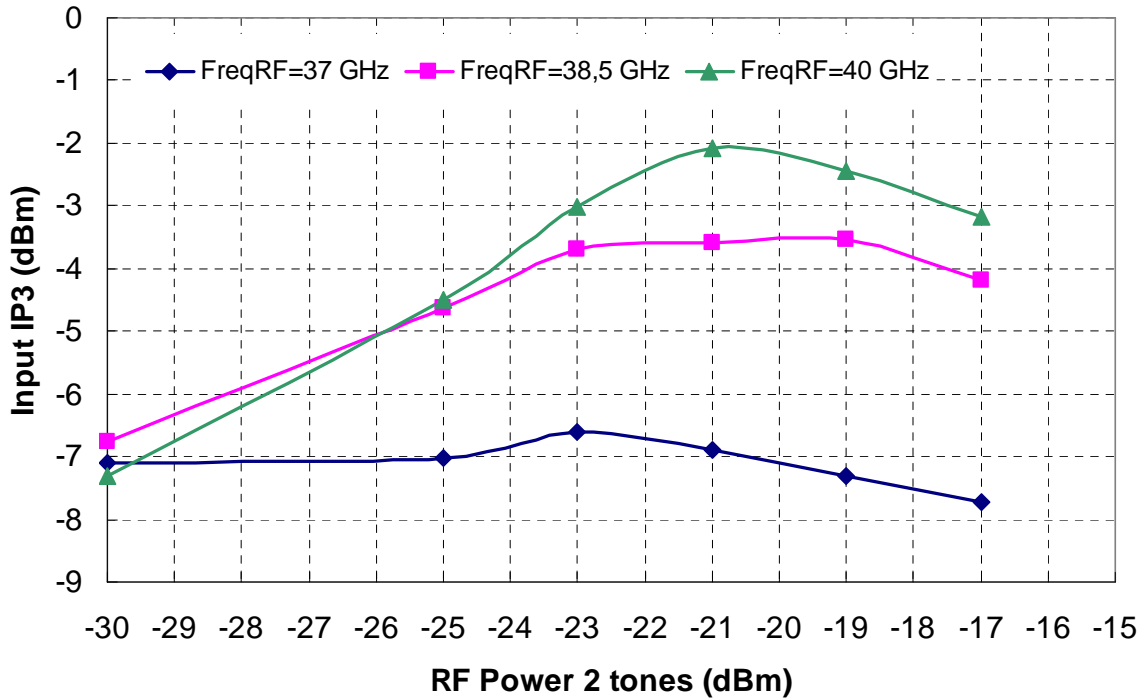


Compression vs P_{RF} (inf. & sup. Mode)
 @ F_{RF}=40GHz & F_{IF}=3GHz & P_{LO}=0 dBm

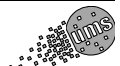
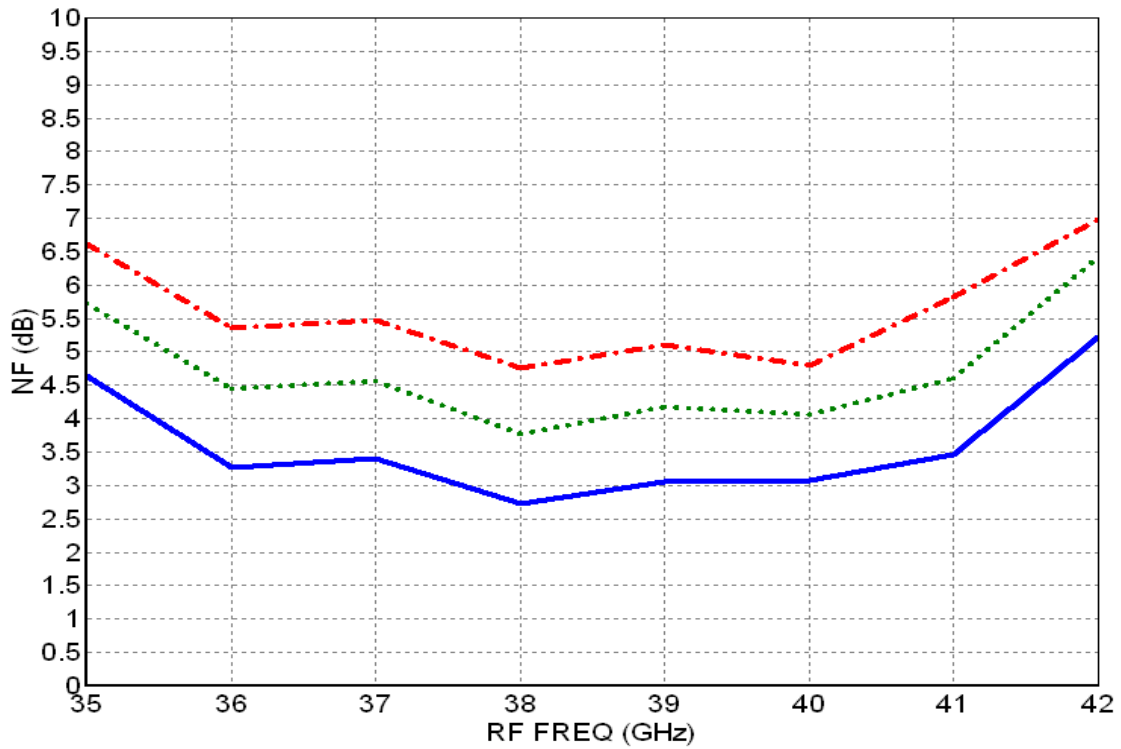


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Input IP3 versus RF Power 2 tones
@ PLO=1dBm & FreqIF=2GHz

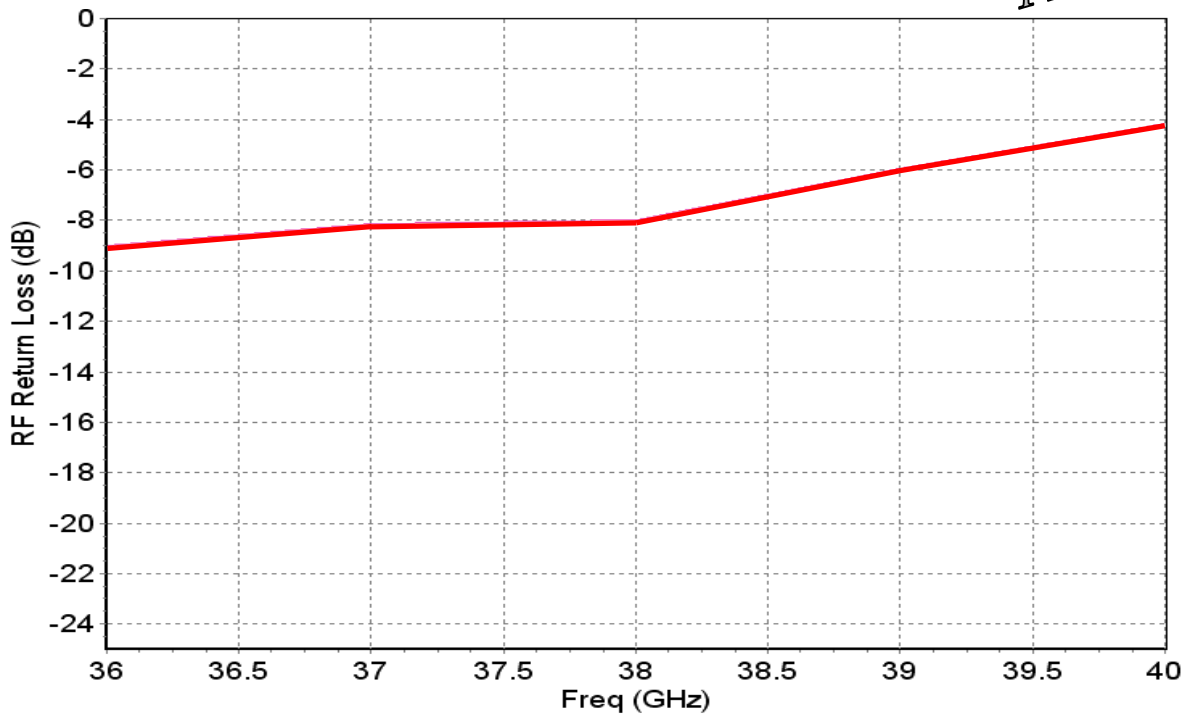


Noise figure versus RF Frequency

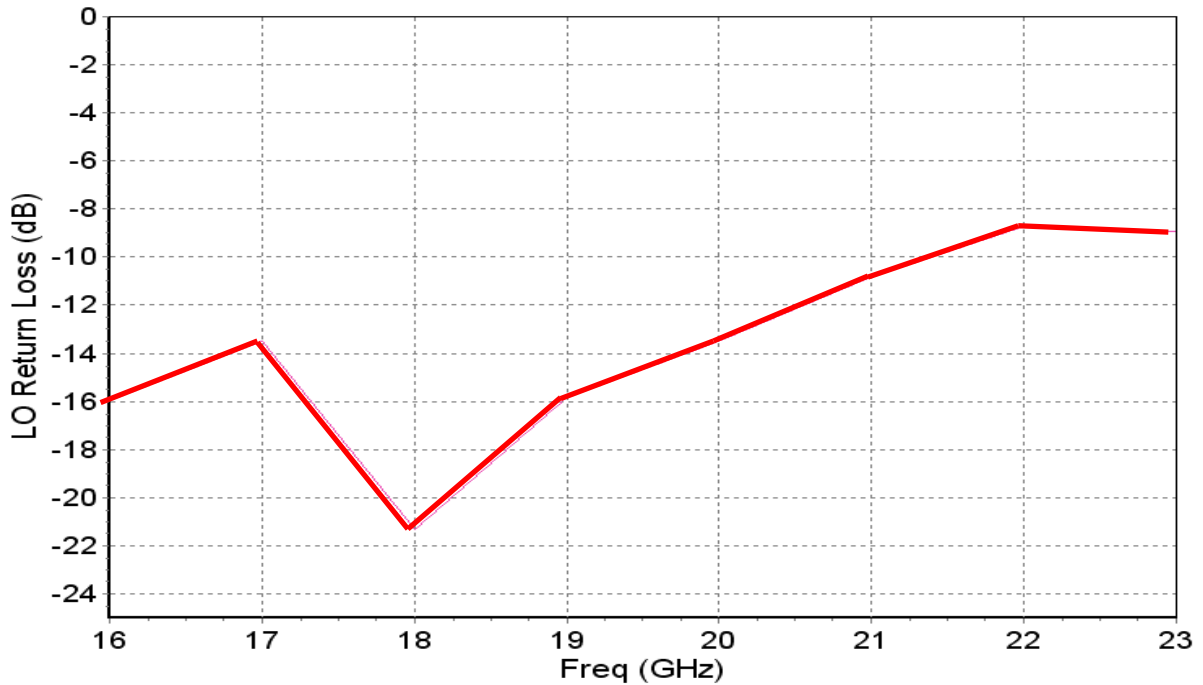


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RF Return Loss versus Frequency

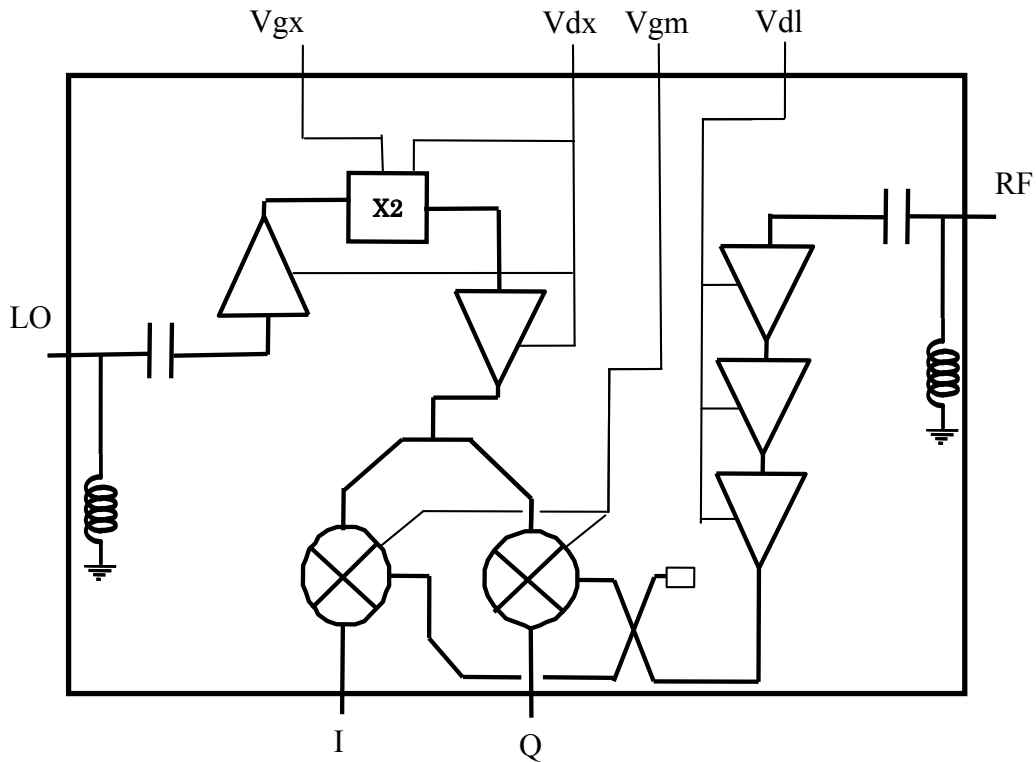


LO Return Loss versus Frequency



*Preliminary***Note :**

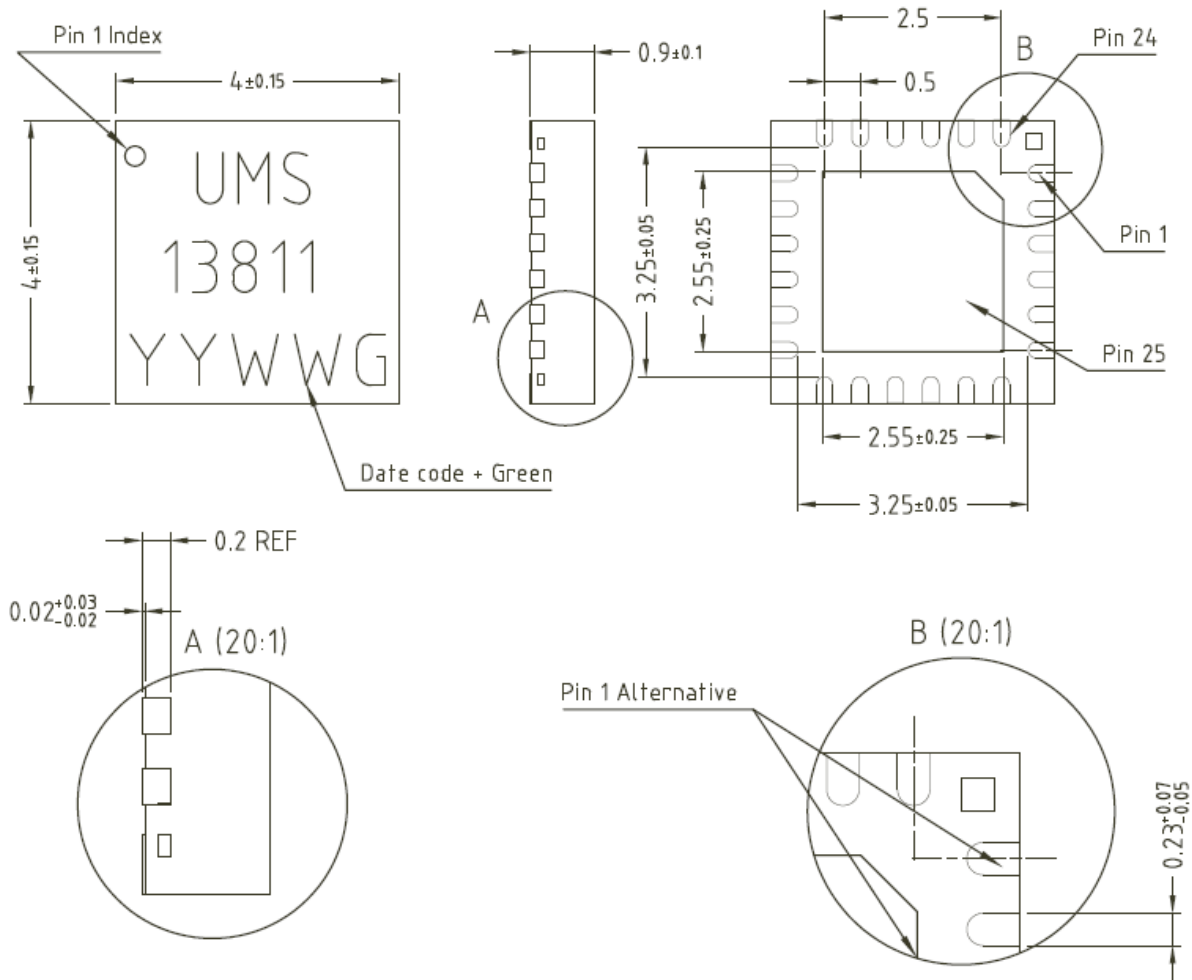
Due to ESD protection, LO and RF accesses are DC grounded, an external capacitance might be requested to isolate the product from external voltage that could be present on the RF accesses.



ESD protections are also implemented on gate accesses : Vgx and Vgm.

Preliminary

Package outline:



Matt tin, Lead Free
 Units
 From the standard
 Pin 25 (paddle): GND

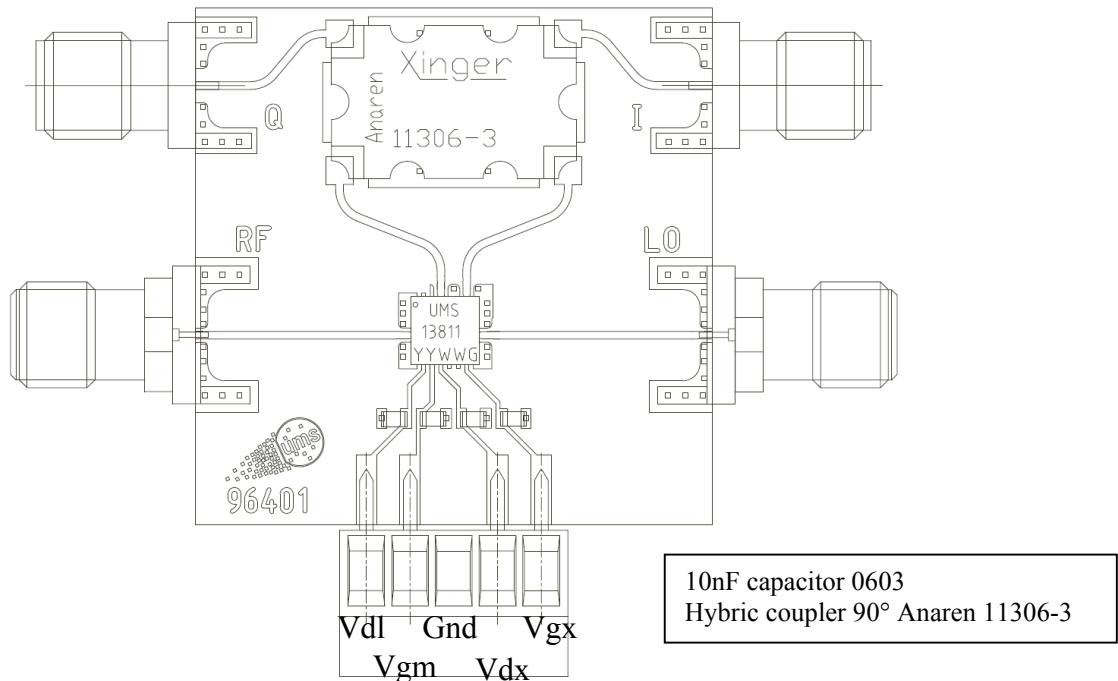
(Green)
 mm
 JEDEC MO-220

- | | |
|----------|--------------|
| 1- NC | 13- GND |
| 2- GND | 14- GND |
| 3- GND | 15- LO IN |
| 4- RF IN | 16- GND |
| 5- GND | 17- GND |
| 6- GND | 18- NC |
| 7- Vdl | 19- I-IF OUT |
| 8- Vgm | 20- GND |
| 9- Vdx | 21- GND |
| 10- NC | 22- Q-IF OUT |
| 11- NC | 23- NC |
| 12- Vgx | 24- NC |

Proposed Assembly board "96401" for the 24L-QFN4x4 product characterization.

Preliminary

- Compatible with the proposed footprint.
- Based on typically Ro4003 / 8mils or equivalent.
- Using a microstrip to coplanar transition to access the package.
- Recommended for the implementation of this product on a module board.



The DC connections do not include any decoupling capacitor in package, therefore it is mandatory to provide a good external DC decoupling on the PC board, as close as possible to the package.

The SMD leadless package has been designed for high volume surface mount PCB assembly process. A typical footprint is proposed for the PCB (motherboard) in the previous drawing. For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017.

Ordering Information

QFN 4x4 RoHS compliant package: MFC-PO13811-QDG/XY
 Stick: XY = 20 Tape & reel: XY = 21

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